

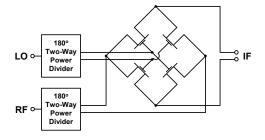
PE4135

Product Description

The PE4135 is a high linearity, passive Quad MOSFET Mixer for GSM800 & Cellular Base Station Receivers, exhibiting high dynamic range performance over a broad LO drive range of up to 20 dBm. This mixer integrates passive matching networks to provide single-ended interfaces for the RF and LO ports, eliminating the need for external RF baluns or matching networks. The PE4135 is optimized for frequency down-conversion using low-side LO injection for GSM800 & Cellular Base Station application, and is also suitable for up-conversion applications.

The PE4135 is manufactured in Peregrine's patented Ultra-Thin Silicon (UTSi®) CMOS process, offering the performance of GaAs with the economy and integration of conventional CMOS.

Figure 1. Functional Schematic Diagram



High Linearity Quad MOSFET Mixer for GSM800 & Cellular BTS

Features

- Integrated, single-ended RF & LO interfaces
- High linearity: IIP3 >+31 dBm, 820 – 920 MHz (+17 dBm LO)
- Low conversion loss: 7.1 dB (+17 dBm LO)
- High isolation: Typical LO-IF at 43 dB, LO-RF at 31.5 dB
- Packaged in a very small 6-lead 3x3mm MLPM

Figure 2. Package Type

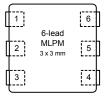


Table 1. Electrical Specifications @ +25°C

Parameter	Minimum	Typical	Maximum	Units
Frequency Range:				
LO	750		850	MHz
RF	820		920	MHz
IF*		70		MHz
Conversion Loss**		6.8		dB
Isolation:				
LO-RF		31.5		dB
LO-IF		43		dB
Input IP3		31.5		dBm
Input 1 dB Compression		21		dBm

^{*}An IF frequency of 70 MHz is a nominal frequency. The IF frequency can be specified by the user as long as the RF and LO frequencies are within the specified maximum and minimum.

^{**}Conversion Loss includes loss of IF transformer (M/A COM ETC1-1-13, nominal loss 0.7 dB at 70 MHz).

Test conditions unless otherwise noted: IF = 70 MHz, LO input drive = 17 dBm, RF input drive = 3 dBm.



Figure 3. Pin Configuration

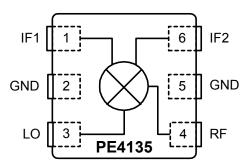


Table 2. Pin Descriptions

Pin No.	Pin Name	Description
1	IF1	IF differential output.
2	GND	Ground connections for Mixer. Traces should be physically short and connect immediately to ground plane for best performance. The exposed solder pad must also be soldered to the ground plane for best performance.
3	LO	LO Input.
4	RF	RF Input.
5	GND	Ground connections for Mixer. Traces should be physically short and connect immediately to ground plane for best performance. The exposed solder pad must also be soldered to the ground plane for best performance.
6	IF2	IF differential output.

Table 3. Absolute Maximum Ratings

Symbol	Parameter/Conditions	Min	Max	Units
T _{ST}	Storage temperature range	-65	150	°C
T_OP	Operating temperature range	-40	85	°C
P _{LO}	LO input power		20	dBm
P_RF	RF input power		16	dBm
V_{ESD}	ESD Sensitive Device		250	V

Electrostatic Discharge (ESD) Precautions

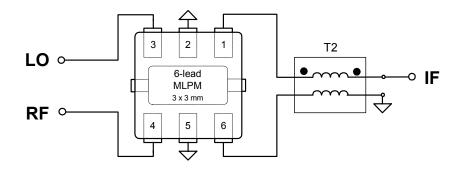
When handling this UTSi device, observe the same precautions that you would use with other ESDsensitive devices. Although this device contains circuitry to protect it from damage due to ESD, precautions should be taken to avoid exceeding the rating specified.

Latch-Up Avoidance

Unlike conventional CMOS devices, UTSi CMOS devices are immune to latch-up.



Figure 4. Evaluation Board Schematic Diagram



T2, M/A-Com E-Series RF 1:1 Transformer, 4.5 – 3000 MHz, ETC1-1-13

Figure 5. Evaluation Board Layout

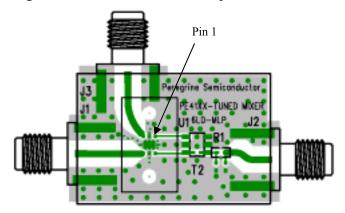
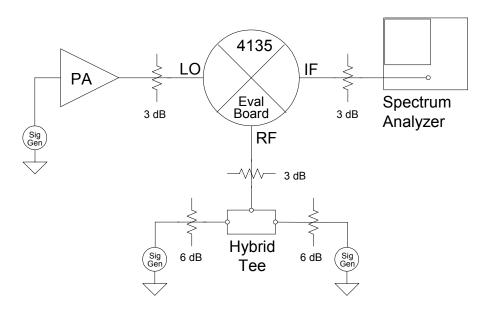


Table 4. Bill of Materials

Reference	Value / Description	
T2	M/A Com ETK1-1-13	
R1	0Ω	
U1	PE4135 MLP Mixer	
J1, J2, J3	SMA Connector	

Figure 6. Evaluation Board Testing Block Diagram, 2-Tone Setup





Typical Performance Data (LO=17 dBm, RF=3 dBm, IF=70 MHz)

Figure 7. Conversion Loss

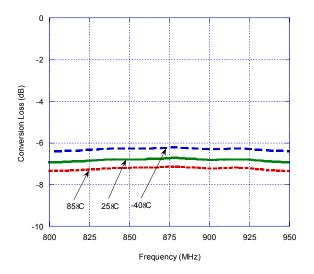


Figure 8. Input 1dB Compression

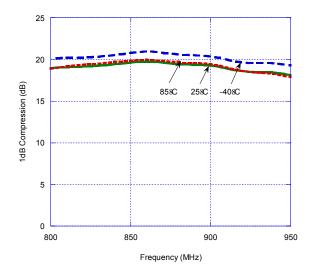


Figure 9. Input IP3 @ -40 °C to 85 °C

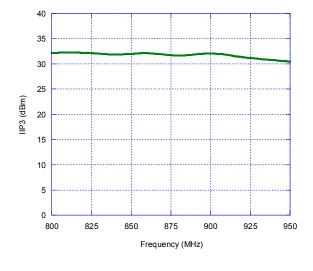
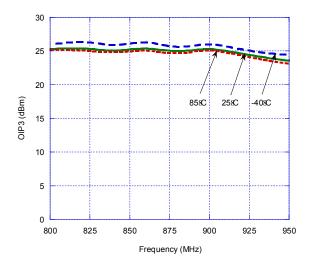


Figure 10. Output IP3





Typical Performance Data (LO=17 dBm, RF=3 dBm, IF=70 MHz)

Figure 11. LO-IF Isolation

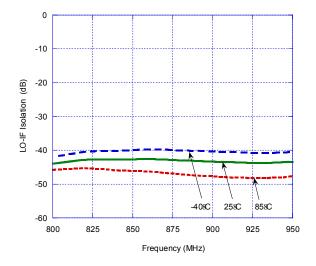


Figure 12. LO-RF Isolation

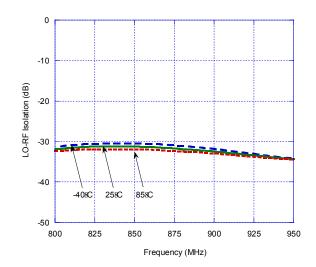


Figure 13. LO Port Return Loss @ 25°C

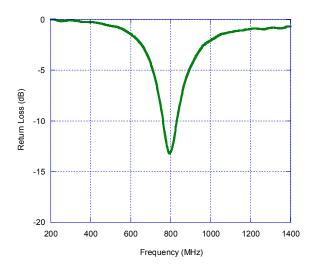


Figure 14. RF Port Return Loss @ 25°C

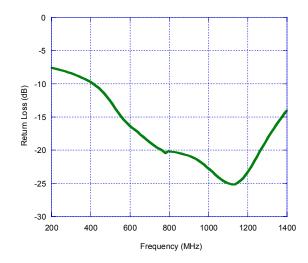


Figure 15. Package Drawing

6-lead MLPM

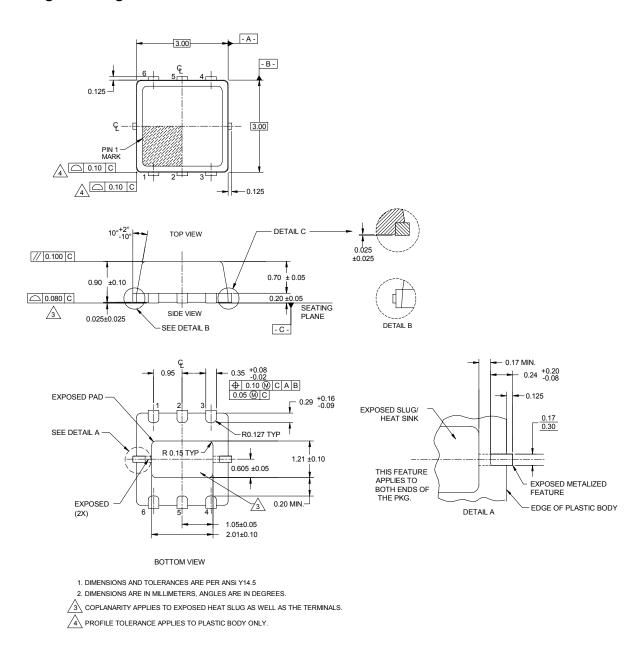


Table 5. Ordering Information

Order Code	Part Marking	Description	Package	Shipping Method
4135-01	4135	PE4135-06MLP3x3-12800F	6-lead 3x3 MLPM	12800 units / Canister
4135-02	4135	PE4135-06MLP3x3-3000C	6-lead 3x3 MLPM	3000 units / T&R
4135-00	4135-EK	PE4135-06MLP3x3-EK	Evaluation Board	1 / Box

File No. 70/0086~01A | UTSi ® CMOS RFIC SOLUTIONS

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Data Sheet Identification

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Preliminary Specification

The data sheet contains preliminary data. Additional data may be added at a later date. Peregrine reserves the right to change specifications at any time without notice in order to supply the best possible product.

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